release of a sacrificial layer a free portion moves out of the plane of the substrate in a self-assembling manner. A sensor is formed on the same substrate, and includes an active layer and contacts. The active layer may be substantially transparent to light at infrared wavelengths. The micro-spring interconnects and the sensor are integrated on the substrate and configured using a compatible manufacturing process.

Please substitute the following amended paragraph for the first full paragraph on page 6:

Spring contacts **20** and **22** are photolithographically patterned on substrate **18** and designed for electrical connections between devices. An inherent stress gradient in each spring contact causes free portions of the spring contacts to bend up and away from the substrate when a sacrificial layer is selectively removed. An anchor portion remains fixed to the substrate. The spring contact is made of an elastic material and the free portions, which are initially fixed, before the sacrificial layer is selectively removed from the substrate, provides for compliant contacts between devices for an electrical interconnection.

Please substitute the following amended paragraph for the fourth full paragraph on page 8:

Turning to stage 2, illustrated by FIGURES 5b and 6b, a hydrogenated amorphous silicon sensor (a-Si:H) component or active layer **44** is grown on top of the first transparent/conductive layer **42**, a-Si:H sensor component **44** is usually comprised of three layers. The first layer **44a**, is a n^+-doped layer of material, typically less than 1,000 angstroms in thickness. Though not limited thereto, the first layer **44a** may be a n^+ phosphorous-doped amorphous silicon, or n^+ arsenic-doped silicon. A second layer **44b** is intrinsic amorphous silicon, of a thickness less than a micron, preferably in the range of 3,000-5,000 angstroms. The third layer **44c** of sensor element **44** is a p^+-doped amorphous silicon of approximately 100 angstroms thickness. An example of a p^+-doped amorphous silicon which may